

NOT RECOMMENDED FOR NEW DESIGN USE DMP2120U



DMP2160U

P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
001/	75mΩ @ V _{GS} = -4.5V	-3.3A
-20V	140mΩ @ V _{GS} = -1.8V	-2.4A

Features and Benefits

- Low On-Resistance
- Very Low Gate Threshold Voltage V_{GS(th)} ≤ 1V
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q 101 Standards for High Reliability

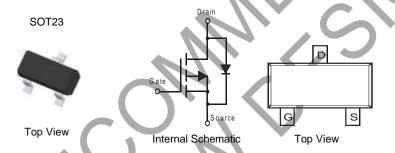
Description and Applications

This MOSFET has been designed to minimize the on-state resistance (R_{DS(on)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Battery Charging
- Power Management Functions
- DC-DC Converters
- Portable Power Adaptors

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.008 grams (approximate)



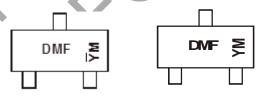
Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2160U-7	SOT23	3000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html

Marking Information



DMF = Marking Code

YM = Date Code Marking for SAT (Shanghai Assembly/ Test site) $\overline{Y}M$ = Date Code Marking for CAT (Chengdu Assembly/ Test site) Y or \overline{Y} = Year (ex: A = 2013)

M = Month (ex: 9 = September)

Chengdu A/T Site

Shanghai A/T Site

Date Code Key

Year	2008		2009	2010		2011	2012		2013	2014		2015
Code	V		W	Х		Υ	Z		Α	В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Drain-Source Voltage	V_{DSS}	-20	V	
Gate-Source Voltage	V _{GSS}	±12	V	
Continuous Drain Current (Note 5) V _{GS} = -4.5V	$T_A = +25$ °C $T_A = +70$ °C	I _D	-3.3 -2.6	А
Pulsed Drain Current		I _{DM}	-13	А

Thermal Characteristics

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P_{D}	1.4	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	90	°C/W
Thermal Resistance, Junction to Case (Note 5)	R ₀ JC	22	°C/W
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C

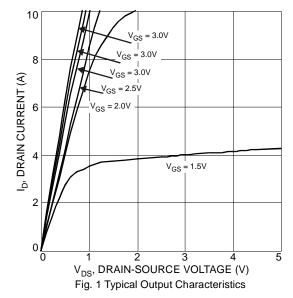
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

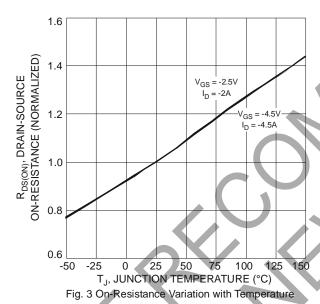
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Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	_	1	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}		1	-1.0	μA	$V_{DS} = -16V, V_{GS} = 0V$
Gate-Source Leakage	Igss		_	±100 ±800	nA	$V_{GS} = \pm 8V, V_{DS} = 0V$ $V_{GS} = \pm 12V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 6)				_	-	
Gate Threshold Voltage	$V_{GS(th)}$	-0.4	-0.6	-0.9	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
			60	75		$V_{GS} = -4.5V, I_D = -1.5A$
Static Drain-Source On-Resistance	R _{DS} (ON)	_	73	96	mΩ	$V_{GS} = -2.5V$, $I_D = -1.2A$
			92	140		$V_{GS} = -1.8V, I_D = -1.2A$
Forward Transconductance	g Fs		7	_	S	$V_{DS} = -10V, I_D = -1.5A$
Diode Forward Voltage (Note 5)	V_{SD}		_	-1.0	V	$V_{GS} = 0V, I_{S} = -1.0A$
DYNAMIC CHARACTERISTICS (Note 7))				
Input Capacitance	C _{iss}	_	627		pF	101/11/01/
Output Capacitance	Coss		64		pF	$V_{DS} = -10V, V_{GS} = 0V$ f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	53	_	pF	1 - 1.01/11/12
Gate Resistance	R _G	_	44.9	_	Ω	$V_{GS} = 0V$, $V_{DS} = 0V$, $f = 1.0MHz$
Total Gate Charge	Q_{g}	_	6.5	_	nC	
Gate-Source Charge	Qgs	_	0.9	_	nC	$V_{GS} = -4.5V$, $V_{DS} = -10V$, $I_{D} = -3A$
Gate-Drain Charge	Q_{gd}	_	1.5	_	nC	
Turn-On Delay Time	t _{D(on)}	_	12.5	_	ns	
Turn-On Rise Time	t _r	_	10.3	_	ns	$V_{DS} = -10V, V_{GS} = -4.5V,$
Turn-Off Delay Time	t _{D(off)}	_	46.5	_	ns	$R_L = 10\Omega$, $R_G = 1.0\Omega$, $I_D = -1A$
Turn-Off Fall Time	t _f	_	22.2	_	ns	

5. Device mounted on 1in^2 FR-4 PCB with 2 oz. Copper. $t \le 10$ sec. Notes:

Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing.







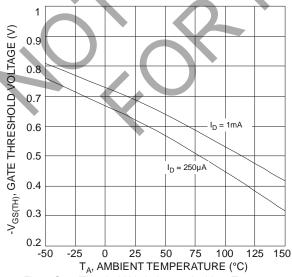
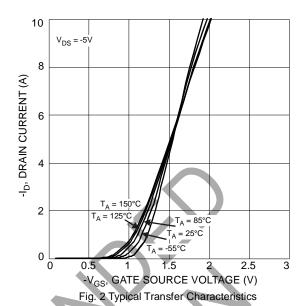
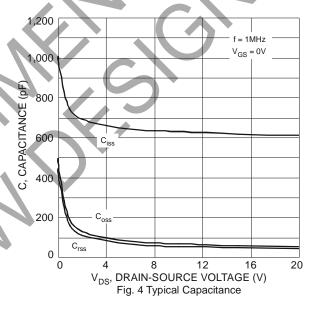


Fig. 5 Gate Threshold Variation vs. Ambient Temperature





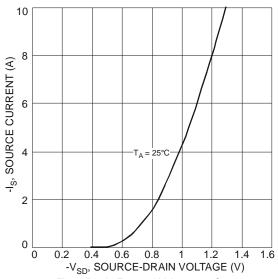
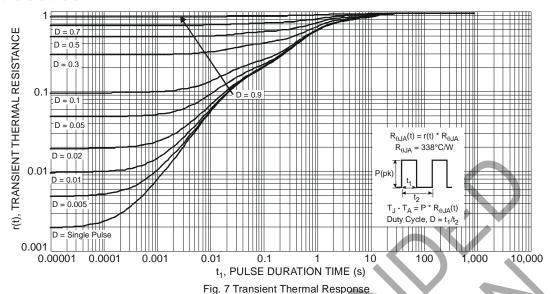


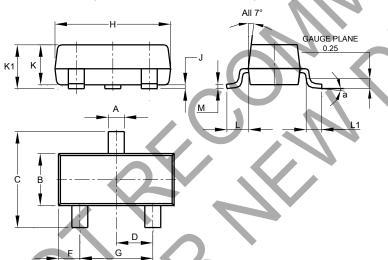
Fig. 6 Diode Forward Voltage vs. Current





Package Outline Dimensions

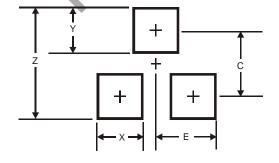
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
M	0.085	0.150	0.110				
α	8°						
All Dimensions in mm							

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35



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